What is claimed is:

1. A method for reducing stress migration in recessed microstructures of a microelectronic wafer comprising the steps of:

subjecting the wafer to a first annealing treatment at 25-300° C; cooling the wafer to room temperature; and subjecting the wafer to a second annealing treatment at 50-400° C.

- 2. The method as recited in claim 1, wherein the temperature of the first annealing treatment is from about 100-300° C.
- 3. The method as recited in claim 1, wherein the temperature of the second annealing treatment is from about 200-400° C.
- 4. The method as recited in claim 1, wherein the temperature of the second annealing treatment is greater than the temperature of the first annealing treatment.
- 5. The method as recited in claim 1, wherein the time duration of the second annealing treatment is greater than that of the first annealing treatment.
- 6. A method for reducing stress migration in recessed microstructures of a microelectronic wafer comprising the steps of:

subjecting the wafer to a first annealing treatment at 25-300° C for from about 10 seconds to about 10 hours;

cooling the wafer to room temperature; and subjecting the wafer to a second annealing treatment at 50-400° C.

7. The method as recited in claim 6, wherein the temperature of the first annealing treatment is from about 100-300° C.

PH1\1087726.1

- 8. The method as recited in claim 6, wherein the temperature of the second annealing treatment is from about 200-400° C.
- 9. The method as recited in claim 6, wherein the temperature of the second annealing treatment is greater than the temperature of the first annealing treatment.
- 10. The method as recited in claim 6, wherein the time duration of the second annealing treatment is greater than that of the first annealing treatment.
- 11. A method for reducing stress migration in recessed microstructures of a microelectronic wafer comprising the steps of:

subjecting the wafer to a first annealing treatment at 25-300° C for from about 10-1000 seconds;

cooling the wafer to room temperature; and subjecting the wafer to a second annealing treatment at 50-400° C.

- 12. The method as recited in claim 11, wherein the temperature of the first annealing treatment is from about 100-300° C.
- 13. The method as recited in claim 11, wherein the temperature of the second annealing treatment is from about 200-400° C.
- 14. The method as recited in claim 11, wherein the temperature of the second annealing treatment is greater than the temperature of the first annealing treatment.
- 15. The method as recited in claim 11, wherein the time duration of the second annealing treatment is greater than that of the first annealing treatment.

PH1\1087726.1 5